

## Description

The PAM2304 uses advanced trench technology to provide excellent RDS(ON) and low gate charge. This device is suitable for use as a load switch or in PWM applications.

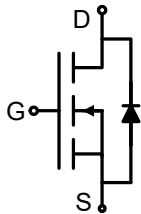
## Features

- ◆ VDS = 30V, ID = 3.6A  
RDS(ON) < 73mΩ @ VGS=4.5V  
RDS(ON) < 58mΩ @ VGS=10V
- ◆ High power and current handling capability
- ◆ Lead free product is acquired
- ◆ Surface mount package

## Applications

- ◆ Battery protection
- ◆ Load switch
- ◆ Power management

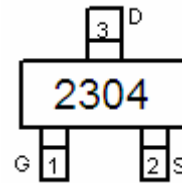
## Dimensions and Pin Configuration



Pin Schematic



SOT-23 top view



2304= Device Marking Code

## Absolute Maximum Ratings (TA=25°C unless otherwise specified)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	I <sub>D</sub>	3.6	A
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	15	A
Maximum Power Dissipation	P <sub>D</sub>	1.7	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 To 150	°C

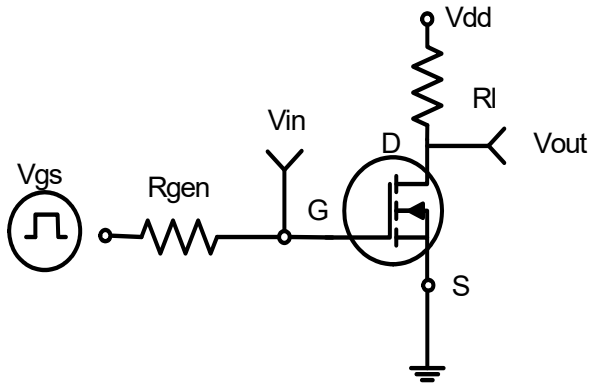
## Ordering Information

Part Number	Marking	Packaging	Reel Size
PAM2304	2304	3000/Tape & Reel	7 inch

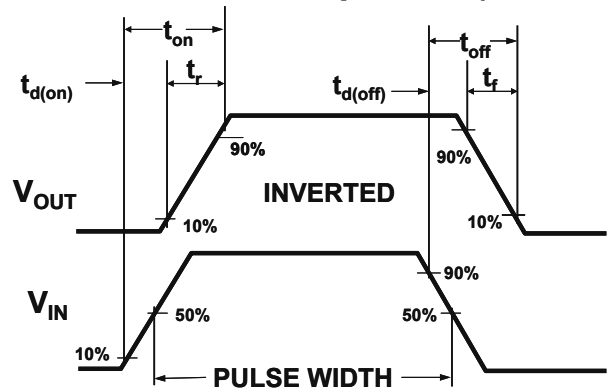
**Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise specified)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.5	2.2	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=3.1A$	-	58	73	m $\Omega$
		$V_{GS}=10V, I_D=3.6A$	-	40	58	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=3.6A$	-	11	-	S
<b>Dynamic Characteristics (Note4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0MHz$	-	230	-	PF
Output Capacitance	$C_{oss}$		-	40	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	17	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=3.6A$ $V_{GS}=4.5V, R_{GEN}=6\Omega$	-	10	-	nS
Turn-on Rise Time	$t_r$		-	50	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	10	-	nS
Turn-Off Fall Time	$t_f$		-	20	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=15V, I_D=3.6A,$ $V_{GS}=10V$	-	4.0	-	nC
Gate-Source Charge	$Q_{gs}$		-	0.75	-	nC
Gate-Drain Charge	$Q_{gd}$		-	0.65	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=2.7A$	-	0.8	1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	1.6	A

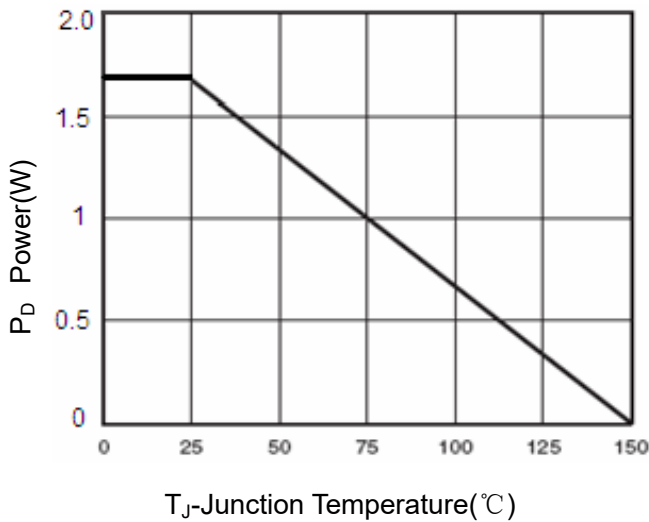
**Typical Performance Characteristics (TA=25°C unless otherwise Specified)**



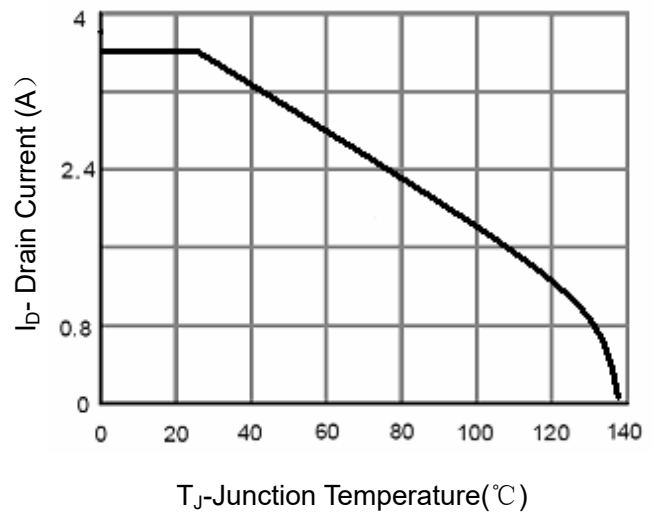
**Figure 1: Switching Test Circuit**



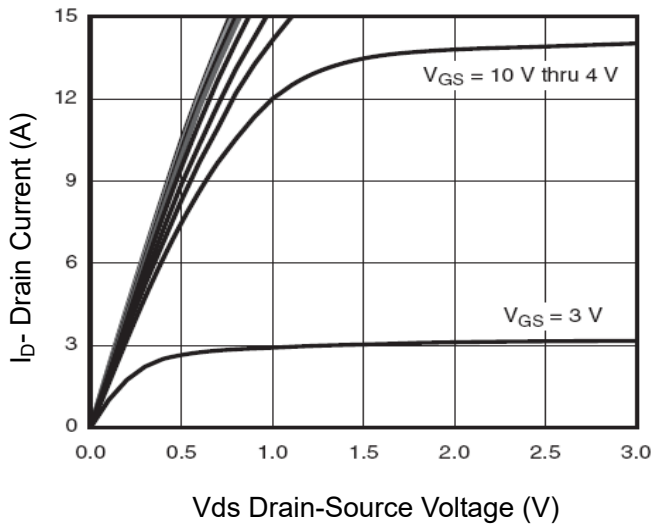
**Figure 2: Switching Waveforms**



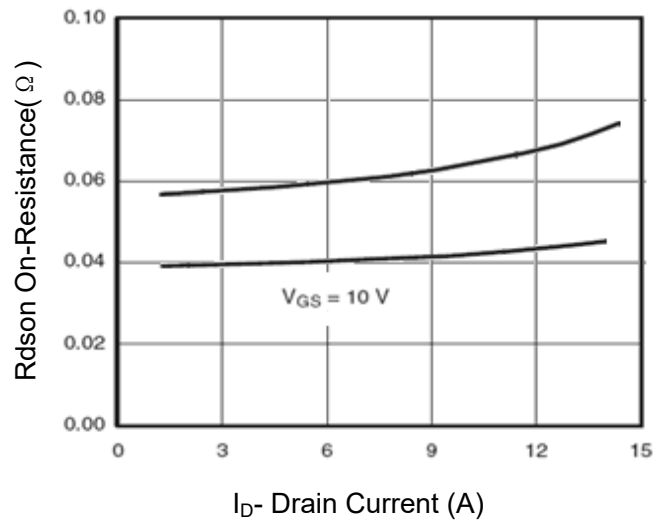
**Figure 3 Power Dissipation**



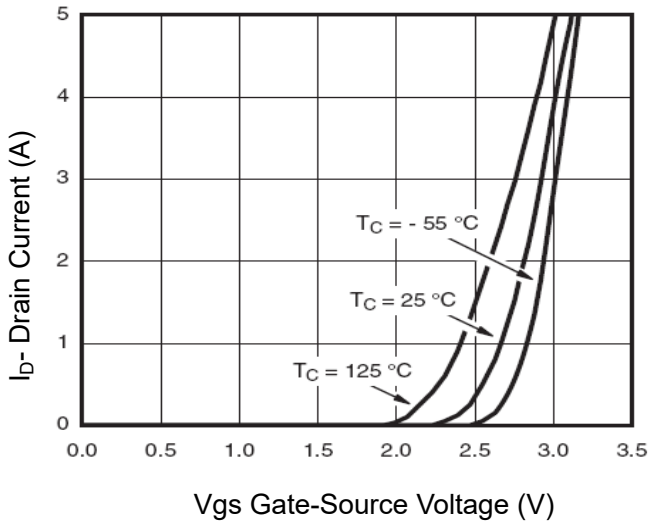
**Figure 4 Drain Current**



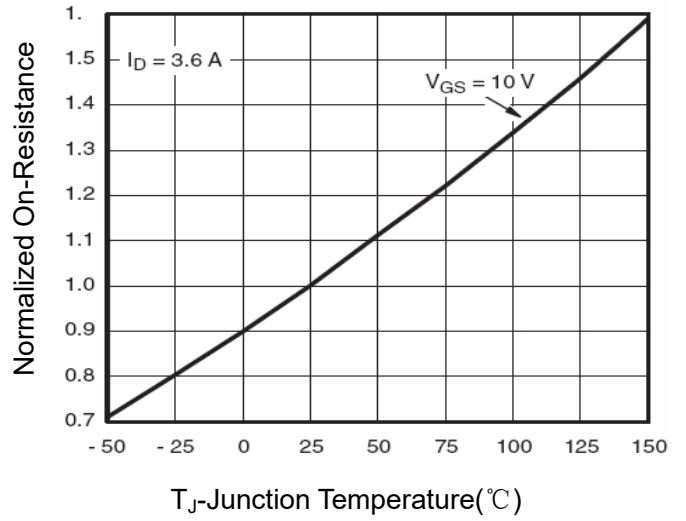
**Figure 5 Output Characteristics**



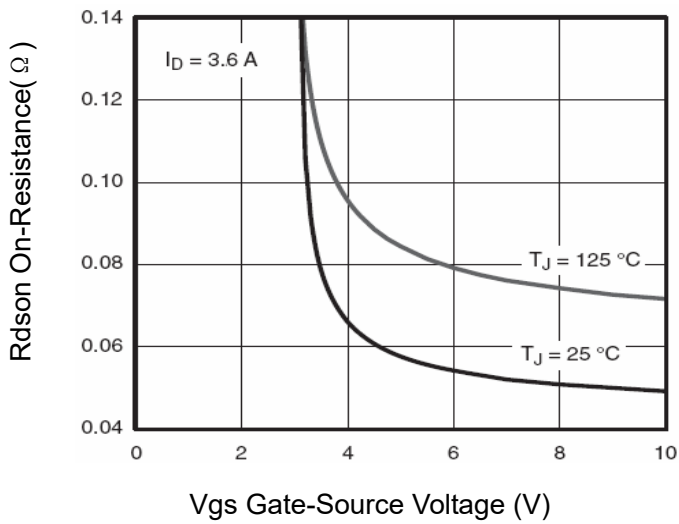
**Figure 6 Drain-Source On-Resistance**



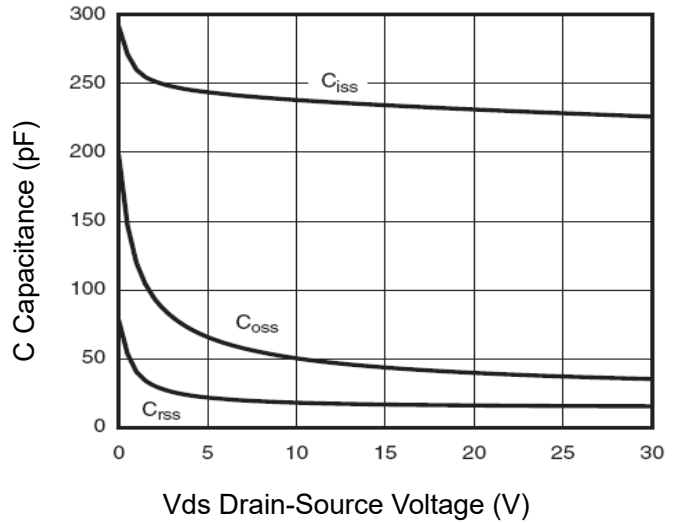
Vgs Gate-Source Voltage (V)  
**Figure 7 Transfer Characteristics**



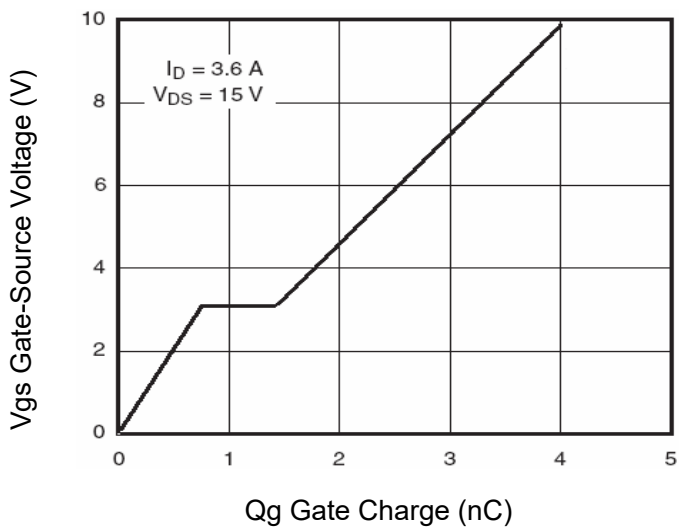
$T_J$ -Junction Temperature( $^\circ\text{C}$ )  
**Figure 8 Drain-Source On-Resistance**



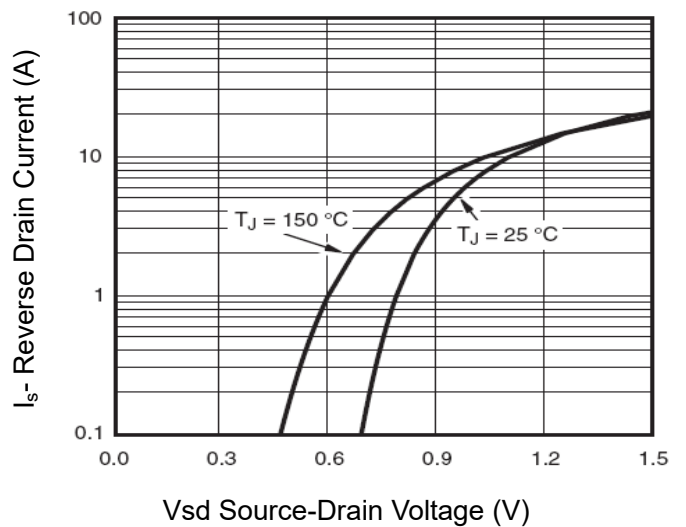
Vgs Gate-Source Voltage (V)  
**Figure 9 Rdson vs Vgs**



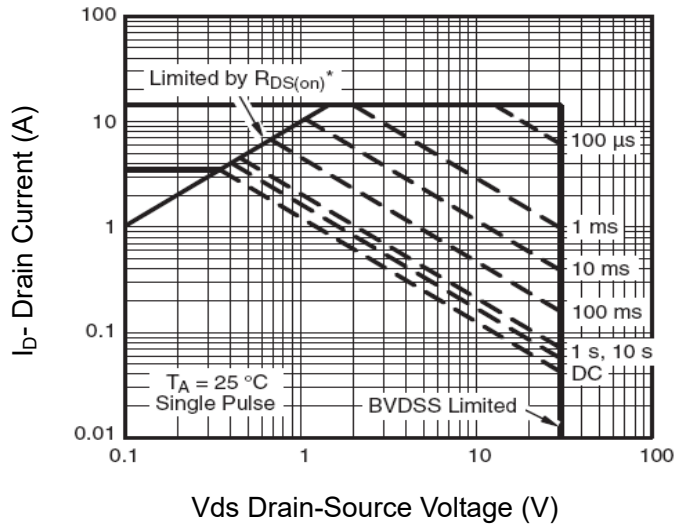
$V_{DS}$  Drain-Source Voltage (V)  
**Figure 10 Capacitance vs Vds**



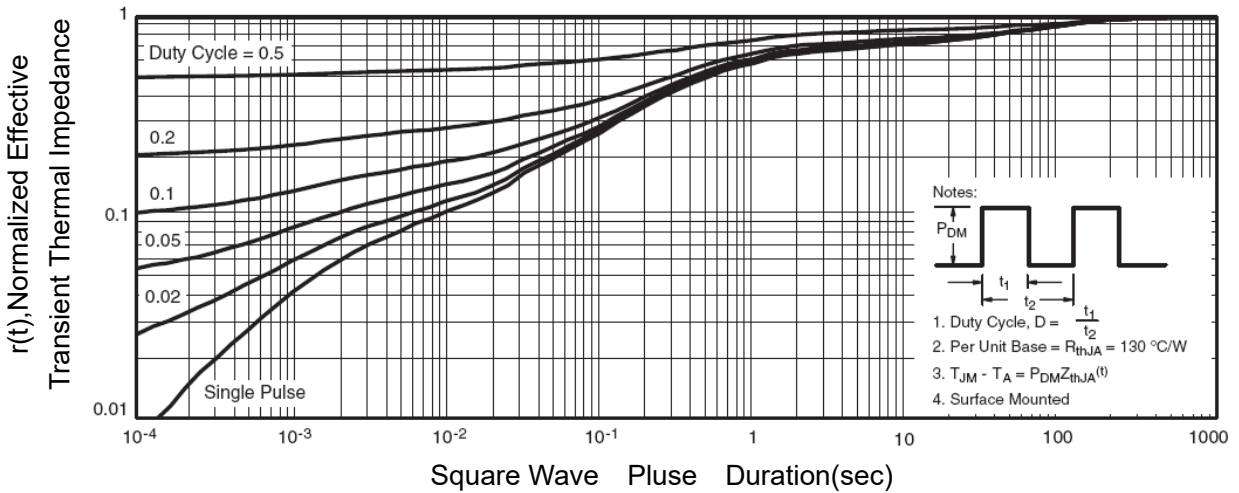
$Q_g$  Gate Charge (nC)  
**Figure 11 Gate Charge**



$V_{SD}$  Source-Drain Voltage (V)  
**Figure 12 Source- Drain Diode Forward**

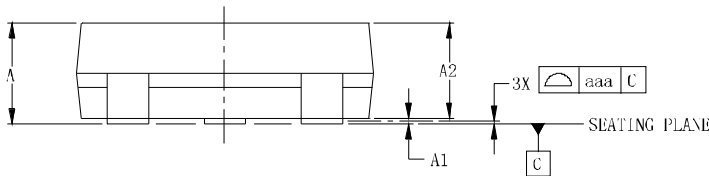
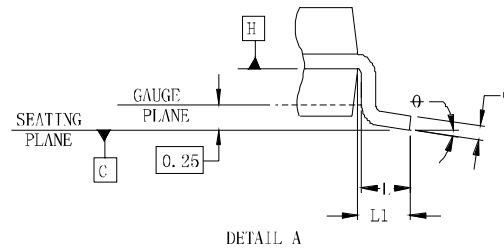
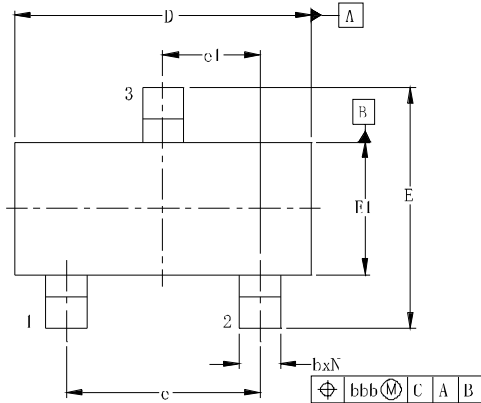


**Figure 13 Safe Operation Area**

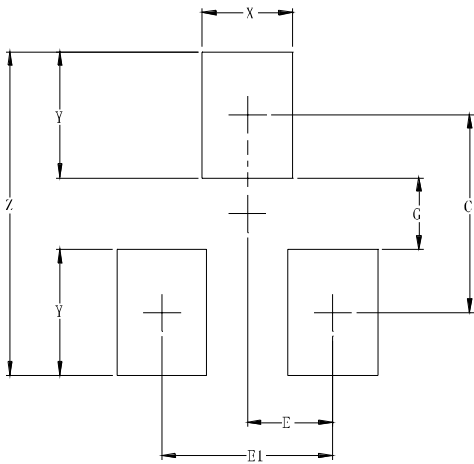


**Figure 14 Normalized Maximum Transient Thermal Impedance**

### SOT-23 Package Outline Drawing



### Suggested Land Pattern



DIMENSIONS						
SYM	INCHES			MILLIMETERS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.035	-	0.044	0.89	-	1.12
A1	0.000	-	0.004	0.01	-	0.10
A2	0.035	0.037	0.040	0.88	0.95	1.02
b	0.012	-	0.020	0.30	-	0.51
c	0.003	-	0.007	0.08	-	0.18
D	0.110	0.114	0.120	2.80	2.90	3.04
E	0.082	0.093	0.104	2.10	2.37	2.64
E1	0.047	0.051	0.055	1.20	1.30	1.40
e	0.075			1.90BSC		
e1	0.037			0.95BSC		
L	0.015	0.020	0.024	0.40	0.50	0.60
L1	0.022			0.55		
N	3			3		
φ	0°	-	8°	0°	-	8°
aaa	0.004			0.10		
bbb	0.008			0.20		

DIMENSIONS		
SYM	INCHES	MILLIMETERS
C	0.087	2.20
E	0.037	0.95
E1	0.075	1.90
G	0.031	0.80
X	0.039	1.00
Y	0.055	1.40
Z	0.141	3.60

### Contact Information

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